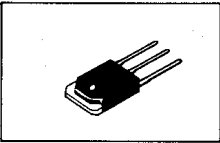


No.1398



2SC3483

NPN Triple Diffused Planar Type Silicon Transistor
 FOR HIGH DEFINITION CRT DISPLAY HORIZONTAL
 DEFLECTION OUTPUT APPLICATIONS

Features:

- High breakdown voltage and high reliability
- High switching speed: $t_f=0.3\mu s$ max.
- Capable of being mounted easily due to one-point fixing type plastic mold package

Absolute Maximum Ratings at $T_a=25^\circ C$

			unit
Collector to Base Voltage	V _{CB0}	1500	V
Collector to Emitter Voltage	V _{CE0}	800	V
Emitter to Base Voltage	V _{EB0}	7	V
Collector Current	I _C	2.5	A
Peak Collector Current	i _{cp}	10	A
Collector Dissipation	P _C T _c =25°C	80	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

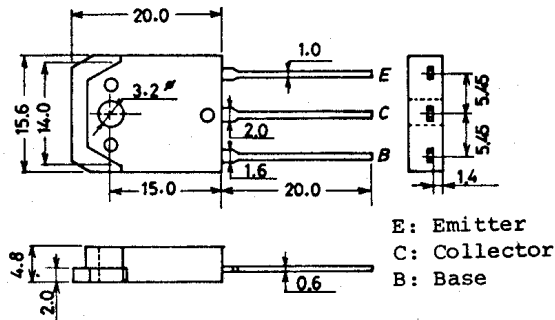
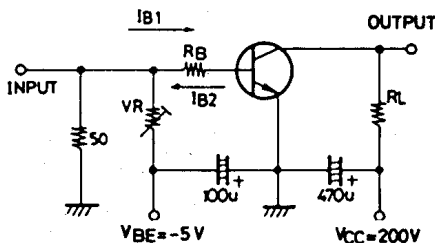
Electrical Characteristics at $T_a=25^\circ C$

		min	typ	max	unit
Collector Cutoff Current	I _{CB0} V _{CB} =800V, I _E =0			10	uA
Emitter Cutoff Current	I _{EB0} V _{EB} =5V, I _C =0			1	mA
DC Current Gain	h _{FE} V _{CE} =5V, I _C =0.5A	8			
Gain Bandwidth Product	f _T V _{CE} =10V, I _C =0.5A		3		MHz
C-E Saturation Voltage	V _{CE(sat)} I _C =2A, I _B =0.6A			8	V
B-E Saturation Voltage	V _{BE(sat)} I _C =2A, I _B =0.6A			1.5	V
C-B Breakdown Voltage	V(BR)CBO I _C =5mA, I _E =0	1500			V
C-E Breakdown Voltage	V(BR)CEO I _C =5mA, R _{BE} =∞	800			V
E-B Breakdown Voltage	V(BR)EBO I _E =5mA, I _C =0	7			V
Storage Time	t _{stg} [I _C =2A, I _{B1} =0.6A,			3.0	us
Fall Time	t _f [I _{B2} =-1.2A,			0.3	us
	[R _L =100ohm]				

Switching Time Test Circuit

Case Outline 2022
(unit:mm)

PW=20us, Duty ≤ 1%



E: Emitter
 C: Collector
 B: Base

This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.